

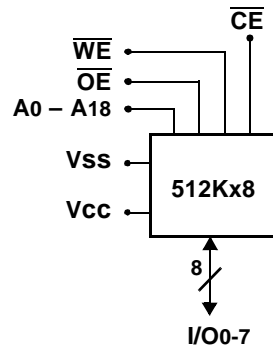
# ACT-PS512K8 High Speed 4 Megabit Plastic Monolithic SRAM

## Plastic Path™ Features

- Low Power Monolithic CMOS 512K x 8 SRAM
- Operating Temperature Range
  - Full Military (-55°C to +125°C)
  - Industrial (-40°C to +85°C)
- Burn-in and Temperature Cycle Available
- 10, 12, 15, 17, 20 & 25ns Access Times
- +5V Power Supply
- Industry Standard Pinouts
  - Center Power / Ground Pins
- TTL Compatible I/O
- 3.3V Device I/O Interfacing
- JEDEC Standard 36 pin Plastic SOJ Package
  - 36 Lead, .93" x .405" x 0.148 Small Outline J lead (SOJ), Aeroflex code# "L2"
- Fully Static Operation
  - No Clocks or Refresh Required



Block Diagram – SOJ (L2)



Pin Description

I/O0-7	Data I/O
A0-18	Address Inputs
$\overline{WE}$	Write Enable
$\overline{CE}$	Chip Enable
$\overline{OE}$	Output Enable
Vcc	Power Supply
Vss	Ground
NC	Not Connected

## General Description

The ACT-PS512K8 is a Plastic High Speed, 4 Megabit (4,194,304 bits) CMOS Monolithic SRAM organized as 524,288 words by 8 bits. Designed for high-speed, high density, high reliability, mass memory and fast cache system applications.

The plastic monolithic is input and output TTL compatible. Writing is executed when the write enable ( $\overline{WE}$ ) and chip enable ( $\overline{CE}$ ) inputs are low. Reading is accomplished when  $\overline{WE}$  is high and  $\overline{CE}$  and output enable ( $\overline{OE}$ ) are both low. Access time grades of 10ns, 12ns, 15ns, 17ns, 20ns and 25ns are standard.

### Absolute Maximum Ratings

Symbol	Parameter	MINIMUM	MAXIMUM	Units
$T_C$	Case Operating Temperature	-55	+125	°C
$T_{STG}$	Storage Temperature	-65	+150	°C
$P_D$	Maximum Package Power Dissipation		1.0	W
$V_G$	Maximum Signal Voltage to Ground	-0.5	$V_{CC} + 0.5$	V
$V_{CC}$	Power Supply Voltage	-0.5	+7.0	V

### Recommended Operating Conditions

Symbol	Parameter	Minimum	Maximum	Units
$V_{CC}$	Power Supply Voltage	+4.5	+5.5	V
$V_{SS}$	Ground	0	0	V
$V_{IH}$	Input High Voltage	+2.2	$V_{CC} + 0.5$	V
$V_{IL}$	Input Low Voltage	-0.5	+0.8	V
$T_C$	Operating Temperature (Military)	-55	+125	°C
$T_C$	Operating Temperature (Industrial)	-40	+85	°C

### Truth Table

Mode	$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	Data I/O	Supply Current
Standby	H	X	X	High Z	$I_{SB}$
Output Disable	L	H	H	High Z	$I_{CC}$
Read	L	H	L	Data OUT	$I_{CC}$
Write	L	L	X	Data IN	$I_{CC}$

### Capacitance

( $V_{IN}$  &  $V_{OUT} = 0V$ ,  $f = 1MHz$ ,  $T_C = 25^\circ C$ , unless otherwise noted, Guaranteed but not tested)

Symbol	Parameter	Maximum	Units
$C_{IN}$	Input Capacitance ( $A_{0-18}$ , $\overline{WE}$ & $\overline{OE}$ )	6	pF
$C_{OUT}$	Output Capacitance ( $I/O_{0-7}$ & $\overline{CE}$ )	8	pF

### DC Characteristics

( $V_{CC} = 5.0V$ ,  $V_{SS} = 0V$ ,  $T_C = -55^\circ C$  to  $+125^\circ C$  or  $-40^\circ C$  to  $+85^\circ C$ )

Parameter	Sym	Conditions	Min	Max	Units
Input Leakage Current	$I_{LI}$	$V_{CC} = Max$ , $V_{IN} = V_{SS}$ to $V_{CC}$	-10	+10	$\mu A$
Output Leakage Current	$I_{LO}$	$\overline{CE} = V_{IH}$ , $\overline{OE} = V_{IH}$ , $V_{OUT} = V_{SS}$ to $V_{CC}$	-10	+10	$\mu A$
Operating Supply Current	$I_{CC}$	$\overline{CE} = V_{IL}$ , $\overline{OE} = V_{IH}$ , $f = 5MHz$ , $V_{CC} = 5.5V$		130	mA
Standby Current	$I_{SB}$	$\overline{CE} = V_{IH}$ , $\overline{OE} = V_{IH}$ , $f = 5MHz$ , $V_{CC} = 5.5V$		20	mA
Output Low Voltage	$V_{OL}$	$I_{OL} = 8 mA$ , $V_{CC} = 4.5V$		0.4	V
Output High Voltage	$V_{OH}$	$I_{OH} = -4 mA$ , $V_{CC} = 4.5V$	2.4		V

Note: DC Test conditions:  $V_{IL} = 0.3V$ ,  $V_{IH} = V_{CC} - 0.3V$ .

## AC Characteristics

(V<sub>CC</sub> = 5.0V, V<sub>SS</sub> = 0V, T<sub>C</sub> = -55°C to +125°C or -40°C to +85°C)

### Read Cycle

Parameter	Sym	-010		-012		-015		-017		-020		-025		Units
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Read Cycle Time	t <sub>RC</sub>	10		12		15		17		20		25		ns
Address Access Time	t <sub>AA</sub>		10		12		15		17		20		25	ns
Chip Enable Access Time	t <sub>ACE</sub>		10		12		15		17		20		25	ns
Output Hold from Address Change	t <sub>OH</sub>	3		3		3		3		4		5		ns
Output Enable to Output Valid	t <sub>OE</sub>		5		6		7		8		10		12	ns
Chip Enable to Output in Low Z (1)	t <sub>CLZ</sub>	3		3		3		3		3		3		ns
Output Enable to Output in Low Z (1)	t <sub>OLZ</sub>	0		0		0		0		0		0		ns
Chip Deselect to Output in High Z (1)	t <sub>CHZ</sub>		5		6		7		7		8		10	ns
Output Disable to Output in High Z (1)	t <sub>OHZ</sub>		5		6		7		7		8		10	ns

Note 1. Guaranteed by design, but not tested

### Write Cycle

Parameter	Sym	-010		-012		-015		-017		-020		-025		Units
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t <sub>WC</sub>	10		12		15		17		20		25		ns
Chip Enable to End of Write	t <sub>CW</sub>	7		8		10		12		13		15		ns
Address Valid to End of Write	t <sub>AW</sub>	7		8		10		12		13		15		ns
Data Valid to End of Write	t <sub>DW</sub>	5		6		8		8		9		10		ns
Write Pulse Width	t <sub>WP</sub>	7		8		10		12		13		15		ns
Address Setup Time	t <sub>AS</sub>	0		0		0		0		0		0		ns
Address Hold Time	t <sub>AH</sub>	0		0		0		0		0		0		ns
Output Active from End of Write (1)	t <sub>OW</sub>	3		3		3		3		4		5		ns
Write to Output in High Z (1)	t <sub>WHZ</sub>		5		6		7		8		8		10	ns
Data Hold from Write Time	t <sub>DH</sub>	0		0		0		0		0		0		ns

Note 1. Guaranteed by design, but not tested

## Data Retention Electrical Characteristics (Special Order Only)

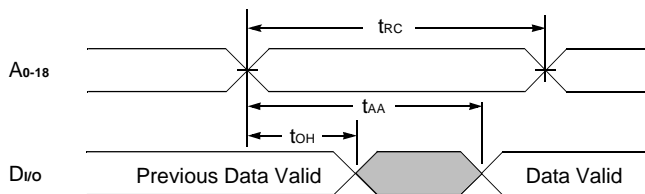
V<sub>CC</sub> = 5.0V, V<sub>SS</sub> = 0V, T<sub>C</sub> = -55°C to +125°C or -40°C to +85°C)

Parameter	Sym	Test Conditions	All Speeds			Units
			Min	Typ	Max	
V <sub>CC</sub> for Data Retention	V <sub>DR</sub>	$\overline{CE} \geq V_{CC} - 0.2V$	2		5.5	V
Data Retention Current	I <sub>CCDR1</sub>	V <sub>CC</sub> = 3V		0.5	2.0	mA

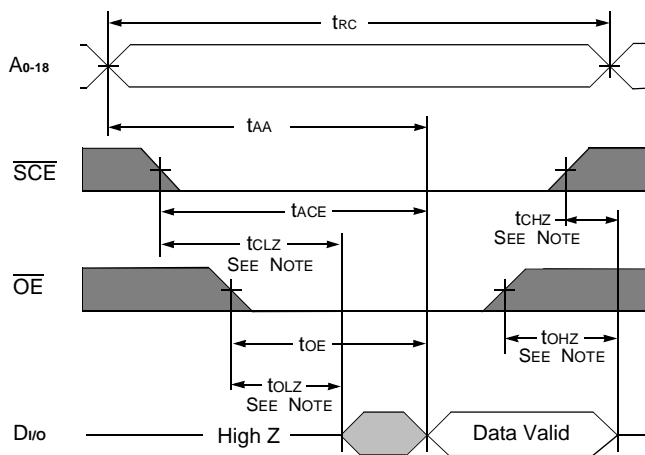
# Timing Diagrams — SRAM

## Read Cycle Timing Diagrams

### Read Cycle 1 ( $\overline{SCE} = \overline{OE} = V_{IL}, \overline{SWE} = V_{IH}$ )

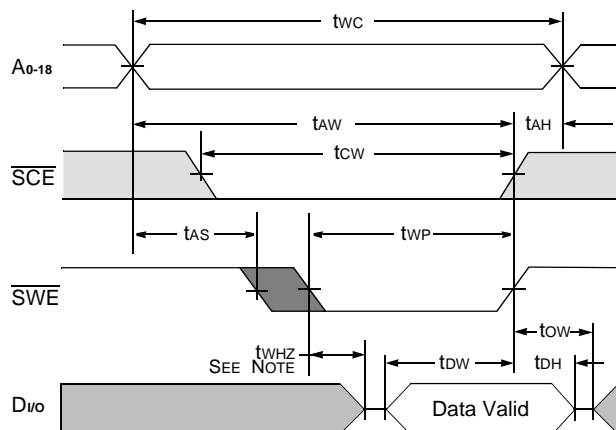


### Read Cycle 2 ( $\overline{SWE} = V_{IH}$ )

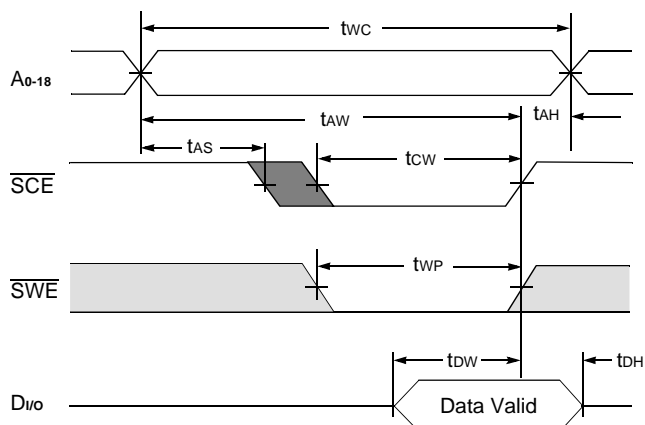


## Write Cycle Timing Diagrams

### Write Cycle ( $\overline{SWE}$ Controlled, $\overline{OE} = V_{IH}$ )

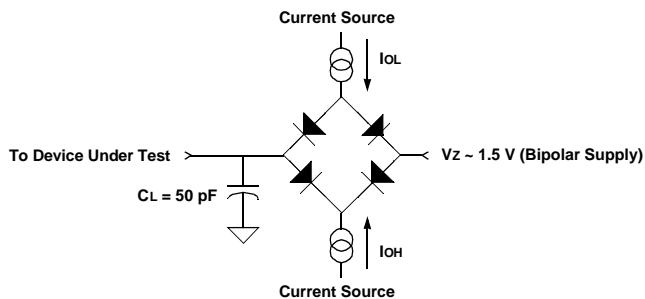


### Write Cycle ( $\overline{SCE}$ Controlled, $\overline{OE} = V_{IH}$ )



Note: Guaranteed by design, but not tested.

## AC Test Circuit



### Notes:

- 1) Vz is programmable from -2V to +7V.
- 2) IoL and IoH programmable from 0 to 16 mA.
- 3) Tester Impedance Zo = 75Ω.
- 4) Vz is typically the midpoint of VOH and Vol.
- 5) IoL and IoH are adjusted to simulate a typical resistance load circuit.
- 6) ATE Tester includes jig capacitance.

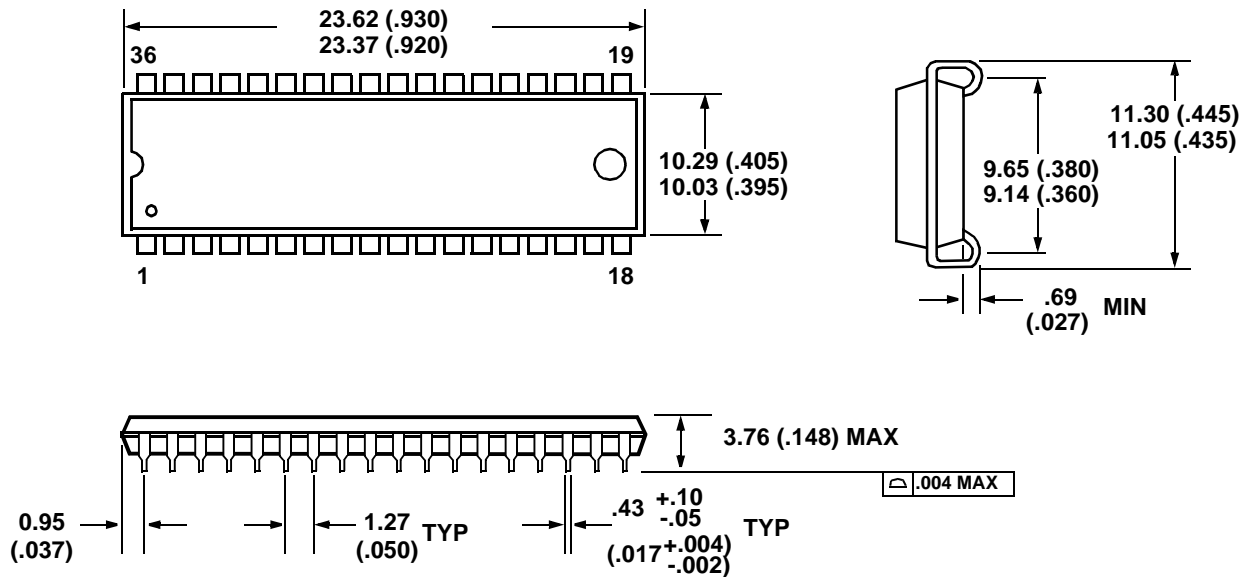
## AC Test Conditions

Parameter	Typical	Units
Input Pulse Level	0 – 3.0	V
Input Rise and Fall	5	ns
Input and Output Timing Reference Level	1.5	V

## Pin Numbers & Functions

36 Pins — SOJ			
Pin #	Function	Pin #	Function
1	A0	19	NC
2	A1	20	A10
3	A2	21	A11
4	A3	22	A12
5	A4	23	A13
6	$\overline{CE}$	24	A14
7	I/O0	25	I/O4
8	I/O1	26	I/O5
9	V <sub>cc</sub>	27	V <sub>cc</sub>
10	V <sub>ss</sub>	28	V <sub>ss</sub>
11	I/O2	29	I/O6
12	I/O3	30	I/O7
13	$\overline{WE}$	31	$\overline{OE}$
14	A5	32	A15
15	A6	33	A16
16	A7	34	A17
17	A8	35	A18
18	A9	36	NC

### Package Outline "L2" — SOJ Package, 36 Leads



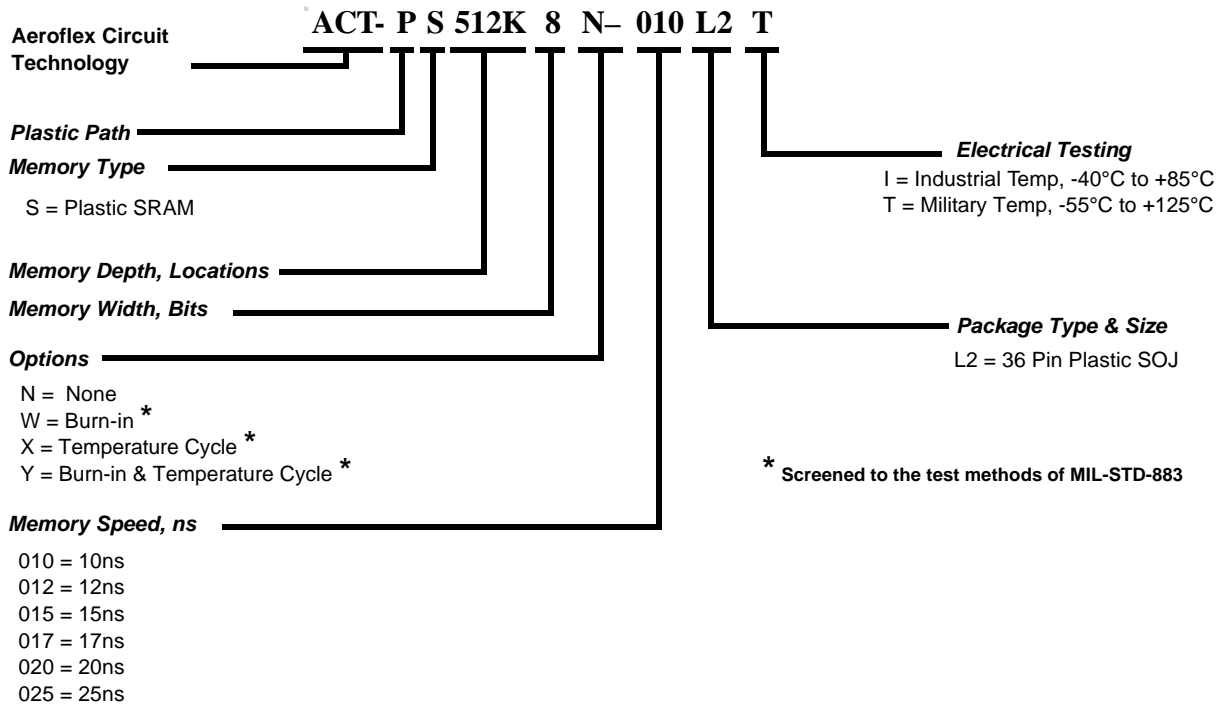
All dimensions in inches  
 Dimensions in millimeters mm  
 Dimensions in inches (.xxx)



### Ordering Information (Typical)

Model Number	Options	Speed	Package
ACT-PS512K8N-010L2I	None	10ns	36 Lead SOJ
ACT-PS512K8W-012L2I	Burn-in	12ns	36 Lead SOJ
ACT-PS512K8X-015L2T	Temp Cycle	15ns	36 Lead SOJ
ACT-PS512K8Y-017L2T	Temp Cycle & Burn-in	17ns	36 Lead SOJ
ACT-PS512K8Y-020L2T	Temp Cycle & Burn-in	20ns	36 Lead SOJ
ACT-PS512K8Y-025L2T	Temp Cycle & Burn-in	25ns	36 Lead SOJ

### Part Number Breakdown



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